ADVANCE PROGRAM

2001 GaAs REL Workshop
SUNDAY October 21, 2000, Preceding the GaAs IC Symposium
Baltimore Salon B, Renaissance Harbor Place, Baltimore, Maryland
SPONSORED BY JEDEC COMMITTEE JC-14.7, EIA, and in cooperation with the IEEE.

Registration (Cost of Workshop is $125 at the door, make checks payable to EIA) 7:30 AM
Welcome, Opening Remarks, Introductions, Start Anthony Immorlica, Workshop Chairman 8:00 AM

SESSION 1 - Non-GaAs and GaAs Comparisons Roberto Menozzi, Session Chair 8:15-9:15 AM
2. Comparison of Silicon Carbide and GaAs Schottky Diode. J. Luo, K. Chung, H. Huang, and J. Bernstein, University of Maryland.

SESSION 2 - Reliability and Defects Sammy Kayali, Session Chair 9:30 – 10:30 AM
2. Effects of Crystal Imperfections in Multiple Quantum Well PIN Optoelectronic Devices and a Method of Restoring Failed Device Characteristics. K. Ikossi, et al., Naval Research Laboratory.

Tutorial - Design for Reliability Concepts for the Electronics Industry Presented by M/A Com
1. Design for Reliability and its Application to the GaAs Marketplace Peter Ersland 10:45-11:15 AM

Lunch NOON-1:10 PM

SESSION 3 - Temperature and Field-accelerated Testing Robert Ferro, Session Chair 1:15-2:35 PM
3. Channel-Substrate Current and Breakdown Characteristics of GaAs MESFETs with Varied MBE Buffer Thickness. F. Gao, R. Chanana, and T. Nicholls, Alpha Industries Inc.

SESSION 4 - HBT Reliability Bill Roesch, Session Chair 2:50-4:15 PM
4. Reliable AlGaAs/GaAs HBTs grown by MBE with increased Beryllium Doping and Aluminum Concentration. M. Fresina, M. Logue, J. Fendrich and T. Rogers, RF Micro Devices.

Late Papers Wallace Anderson, Technical Program Chairman 4:25 PM

Website: http://www.jedec.org/home/gaas/